



GBU20005-GBU2010/G

Single Phase 20.0Amp Glass passivated Bridge Rectifiers

Features

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- Idea for printed circuit board
- · Glass passivated Junction chip
- · Low reverse leakage
- High forward surge current capability
- High temperature soldering guaranteed 250°C/10 seconds at terminals
- The G suffix is uses for photoresist chip, otherwise it is a knife scraping chip

MECHANICAL DATA

- Case: Molded plastic body
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity: Polarity symbol marking on body
- Mounting Position: Any

Maximum Ratings And Electrical Characteristics (@T_A=25°C unless otherwise noted)

Symbol	Parameter	GBU 20005	GBU 2001	GBU 2002	GBU 2004	GBU 2006	GBU 2008	GBU 2010	Unit
V _{RRM}	repetitive peak reverse voltage	50	100	200	400	600	800	1000	V
V _{RMS}	RMS voltage	35	70	140	280	420	560	700	V
V _{DC}	DC blocking voltage	50	100	200	400	600	800	1000	V
I _{AV}	Maximum average forward rectified current with heatsink	20.0					A		
I _{FSM}	Peak forward surge current, 8.3ms single half sine-wave	220.0				А			
l ²	I_t^2 Rating for fusing (t=8.3ms,T_A=25°C)	200.86					A _S ²		
V _F	Forward Voltage at 10.0A	1.10				V			
I _R	Peak Reverse Current@T _A =25°C	5.0						uA	
	at rated DC blocking voltage@ T_A =125°C	500							
CJ	Typical junction capacitance (Note 1)	70			pF				
R_{qJA}	Typical thermal resistance	26			°C/W				
TJ	Operation Temperature Range	-55 to +150					- °C		
T _{STG}	Storage Temperature Range	-55 to +150							

Note:(1)Measured at 1MHz and applied reverse voltage of 4.0V D.C.

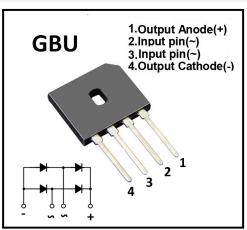
(2)Mounted on glass epoxy PC board with 1.3mm² solder pad.

(3) Device mounted on 50mm x 50mm x 1.6mm Cu Plate Heatsink.

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Mechanical Data







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Ratings And Characteristic Curves

Figure 1: DERATING CURVE OUTPUT RECTIFIED CUR-

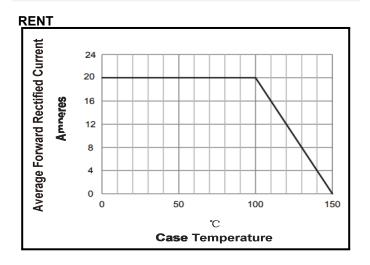


Figure 3: TYPICAL FORWARD VOLTAGE CHARACTER-

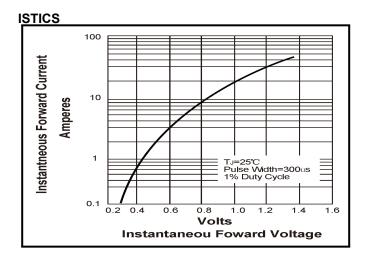
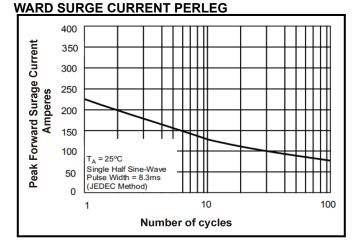
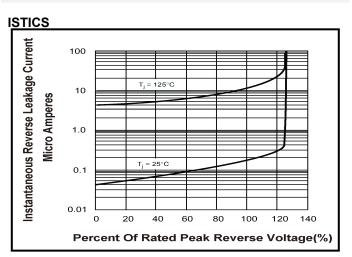


Figure 2: MAXIMUM NON-REPETITIVE PEAK FOR-







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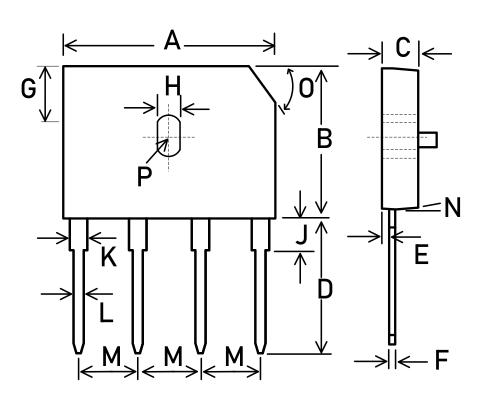




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Outline Drawing -GBU



SYMDOL	MILLIMETER				
SYMBOL	MIN.	MAX.			
A	21.80	22.30			
В	18.30	18.80			
С	3.30	3.60			
D	17.50	18.00			
E	0.76	1.00			
F	0.45	0.55			
G	7.40	7.90			
Н	3.50	4.10			
I	1.65	2.16			
J	2.25	2.75			
К	2.00	2.40			
L	1.00	1.30			
М	4.83	5.33			
N	7.0° TYP.				
0	(3.2)x45°				
Р	1.90PADIUS				

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Specifications are subject to change without notice. Please refer to http://www.born-tw.com for current information. Revision: 2022-Jan-1



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